CRMTGH1503A

N-Channel 150V, 3.47mΩ Typ. Power MOSFET

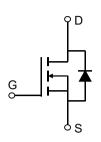
Description

Features

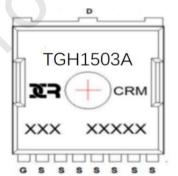
150V, 210A

$$R_{DS(ON)}$$
 Typ = 3.47m Ω @ V_{GS} = 10V

- Advanced Split Gate Trench Technology
- Excellent R_{DS(ON)} and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔVds TESTED!







Marking and Pin Assignment

Application

- Load Switch
- PWM Application
- Power Management

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMTGH1503A	CRMTGH1503A	TOLL	TAPING	13"	2000	10000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		150	V
V_{GS}	Gate-to-Source Voltage		±20	V
	Continuous Drain Current	T _C = 25°C	210	А
I _D	Continuous Diam Current	T _C = 100°C	126	А
I _{DM}	Pulsed Drain Current (1)		840	А
E _{AS}	Single Pulsed Avalanche Energy (2)		1024	mJ
P_{D}	Power Dissipation	T _C = 25°C	417	W
$R_{ heta JC}$	Thermal Resistance, Junction to Case		0.3	°C/W
T_J,T_STG	Junction & Storage Temperature Range		-55 to 150	°C

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Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Chara	acteristics					
V _{(BR)DSS}	Drain-Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	150	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 150V, V _{GS} = 0V	-	-	1.0	μА
I _{GSS}	Gate-Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	±100	nA
On Chara	acteristics					
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	3.2	4	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽³⁾	$V_{GS} = 10V, I_D = 20A$	-	3.47	4.5	mΩ
Dynamic	Characteristics					
C _{iss}	Input Capacitance		-	6213	-	pF
C_{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 25V,$ f = 1MHz		4019	-	pF
C_{rss}	Reverse Transfer Capacitance	1 - 1101112	-	237	-	pF
Q_g	Total Gate Charge		-	90	-	nC
Q_gs	Gate Source Charge	$V_{GS} = 0 \text{ to } 10V$ $V_{DS} = 75V, I_{D} = 80A$) -	25	-	nC
Q_{gd}	Gate Drain("Miller") Charge	V _{DS} - 73V, I _D - 60A	-	20	-	nC
Switchin	g Characteristics					
t _{d(on)}	Turn-On DelayTime		-	20	-	ns
t _r	Turn-On Rise Time	$V_{GS} = 10V, V_{DD} = 75V$	-	40	-	ns
$t_{\text{d(off)}}$	Turn-Off DelayTime	$I_D = 80A$, $R_{GEN} = 3\Omega$	-	59	-	ns
t_{f}	Turn-Off Fall Time		-	45	-	ns
Drain-So	urce Diode Characteristics and M	/lax Ratings				
I _s	Maximum Continuous Drain to Source Diode Forward Current		-	-	210	Α
I _{sm}	Maximum Pulsed Drain to Source Diode	Forward Current	-	-	840	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 20A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	1 004 177 10047	-	103	-	ns
Qrr	Body Diode Reverse Recovery Charge	$I_F = 80A$, di/dt = 100A/us	-	431	_	nC

Notes:

^{1.} Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

^{2.} E_{AS} condition: Starting T_J =25°C, V_{DD} =75V, V_G =10V, R_G =25ohm, L=0.5mH, I_{AS} =64A

^{3.} Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%.

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Test Circuit

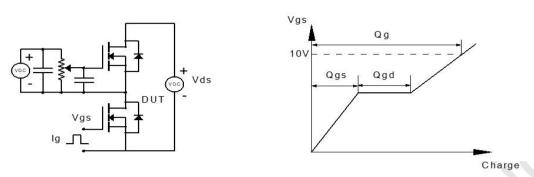


Figure 1: Gate Charge Test Circuit & Waveform

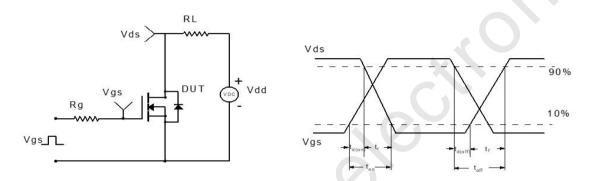


Figure 2: Resistive Switching Test Circuit & Waveform

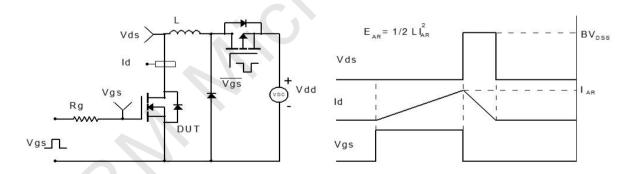


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

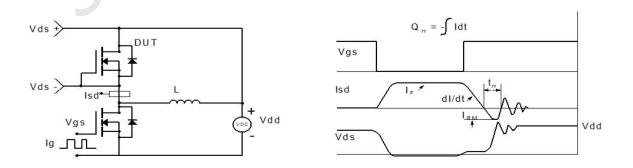
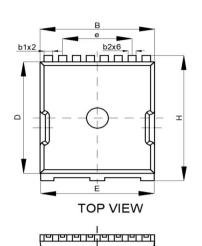


Figure 4: Diode Recovery Test Circuit & Waveform

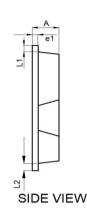
CRMTGH1503A

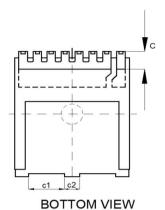
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Package Mechanical Data(TOLL)



FRONT VIEW





SYMBOL	MIN NOM		MAX	
Α	2.20	2.30	2.40	
В	9.85	9.90	9.95	
С	1.50	1.60	1.70	
D	10.40	10.50	10.60	
E	9.75	9.80	9.85	
Н	11.60	11.70	11.80	
L1	0.55	0.65	0.75	
L2	0.65	0.70	0.75	
Ф	6.0BSC			
e1	0.45	0.50	0.55	
b1	0.70	0.75	0.80	
b2	0.60	0.70	0.80	
c1	3.00	3.10	3.20	
c2	1.10	1.20	1.30	
θ	11°			

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